Magnetic memory device

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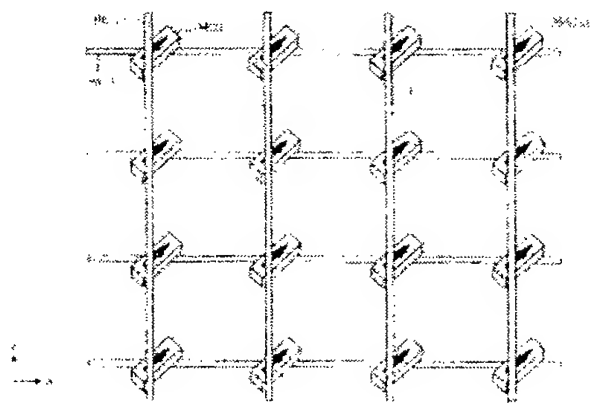
Abstract of **TW 548656 (B)**

A plurality of word lines (WL1) are provided in parallel to one another and a plurality of bit lines (BL1) are provided in parallel to one another, intersecting the word lines (WL1) thereabove. MRAM cells (MC2) are formed at intersections of the word lines and the bit lines therebetween. MRAM cells (MC3) are provided so that an easy axis indicated by the arrow has an angle of 45 degrees with respect to the bit lines and the word lines. Thus, an MRAM capable of cutting the power consumption in writing is achieved and further an MRAM capable of reducing the time required for erasing and writing operations is achieved.



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